

Appl. No.: 09/833,372

Amdt. dated: 10/24/2003

Reply to Office Action of March 20, 2003

In The Specification:

Please amend paragraph [0005] on page 2 as follows:

[0005] In a homojunction bipolar transistor, holes are ejected [from] into the emitter layer [into] from the base layer as a result of the forward biased emitter junction. The injection of holes [into] from the base layer results in a lower cut off frequency and lower current gain of the device resulting in lower efficiency and a lower frequency of operation of the device. In order to reduce the hole injection, the base p-doping is normally made lower than the emitter. Unfortunately, such a configuration results in a base layer with more resistance which, in turn, reduces the output power of the device.